

# HAT2027R

Silicon N Channel Power MOS FET  
High Speed Power Switching

# HITACHI

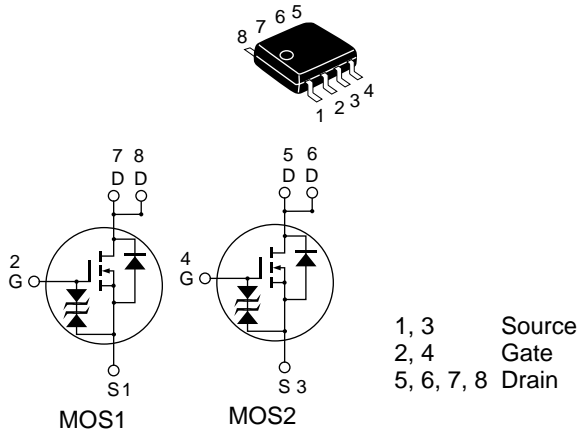
ADE-208-458 E (Z)  
6th. Edition  
February 1999

## Features

- Low on-resistance
- Capable of 2.5 V gate drive
- Low drive current
- High density mounting

## Outline

SOP-8



## Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	20	V
Gate to source voltage	$V_{GSS}$	$\pm 12$	V
Drain current	$I_D$	7	A
Drain peak current	$I_{D(pulse)}$ <sup>Note1</sup>	56	A
Body-drain diode reverse drain current	$I_{DR}$	7	A
Channel dissipation	Pch <sup>Note2</sup>	2	W
Channel dissipation	Pch <sup>Note3</sup>	3	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	- 55 to + 150	°C

Note: 1.  $PW \leq 10\mu s$ , duty cycle  $\leq 1\%$

2. 1 Drive operation : When using the glass epoxy board (FR4 40 x 40 x 1.6 mm),  $PW \leq 10s$

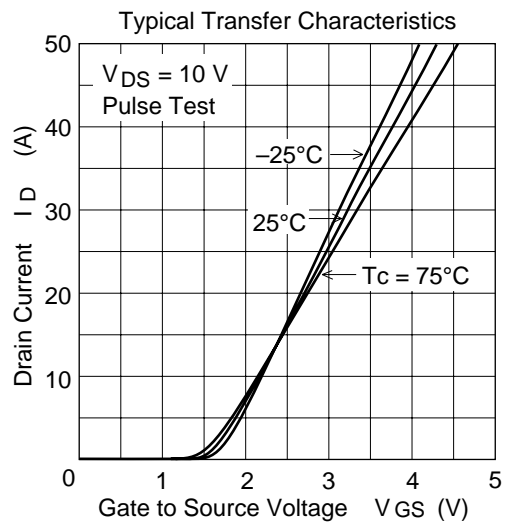
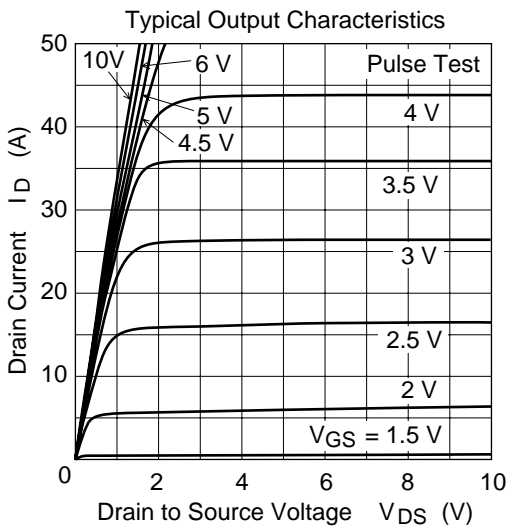
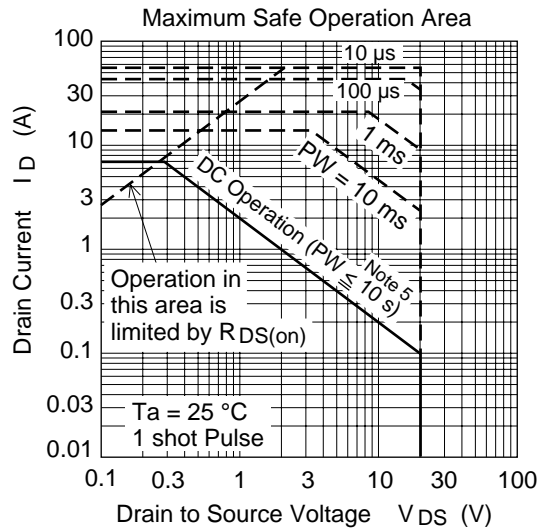
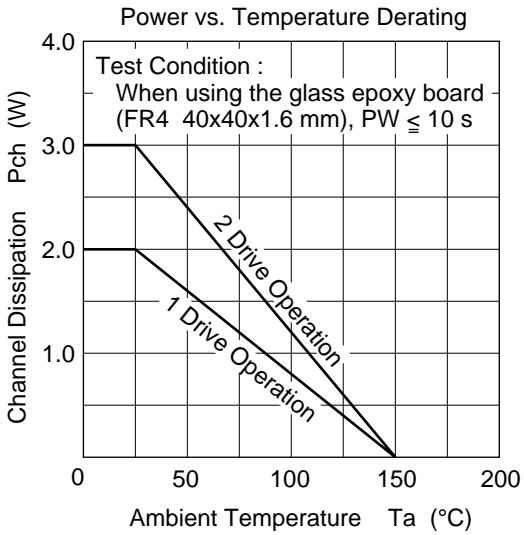
3. 2 Drive operation : When using the glass epoxy board (FR4 40 x 40 x 1.6 mm),  $PW \leq 10s$

## Electrical Characteristics (Ta = 25°C)

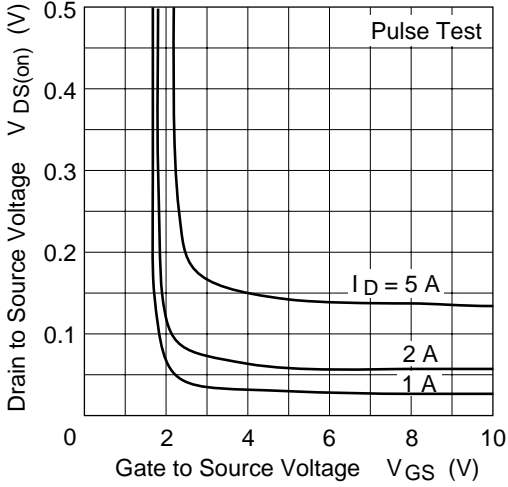
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	20	—	—	V	$I_D = 10\text{ mA}$ , $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	$\pm 12$	—	—	V	$I_G = \pm 100\ \mu A$ , $V_{DS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	$\pm 10$	$\mu A$	$V_{GS} = \pm 10\text{ V}$ , $V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	10	$\mu A$	$V_{DS} = 20\text{ V}$ , $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	0.5	—	1.5	V	$V_{DS} = 10\text{ V}$ , $I_D = 1\text{ mA}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.03	0.038	$\Omega$	$I_D = 4\text{ A}$ , $V_{GS} = 4\text{ V}$ <sup>Note4</sup>
	$R_{DS(on)}$	—	0.038	0.053	$\Omega$	$I_D = 4\text{ A}$ , $V_{GS} = 2.5\text{ V}$ <sup>Note4</sup>
Forward transfer admittance	$ y_{fs} $	9	14	—	S	$I_D = 4\text{ A}$ , $V_{DS} = 10\text{ V}$ <sup>Note4</sup>
Input capacitance	Ciss	—	720	—	pF	$V_{DS} = 10\text{ V}$
Output capacitance	Coss	—	450	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	—	185	—	pF	$f = 1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	—	28	—	ns	$V_{GS} = 4\text{ V}$ , $I_D = 4\text{ A}$
Rise time	$t_r$	—	145	—	ns	$V_{DD} \cong 10\text{ V}$
Turn-off delay time	$t_{d(off)}$	—	100	—	ns	
Fall time	$t_f$	—	125	—	ns	
Body-drain diode forward voltage	$V_{DF}$	—	0.9	1.4	V	$IF = 7\text{ A}$ , $V_{GS} = 0$ <sup>Note4</sup>
Body-drain diode reverse recovery time	$t_{rr}$	—	60	—	ns	$IF = 7\text{ A}$ , $V_{GS} = 0$ $diF/dt = 20\text{ A}/\mu s$

Note: 4. Pulse test

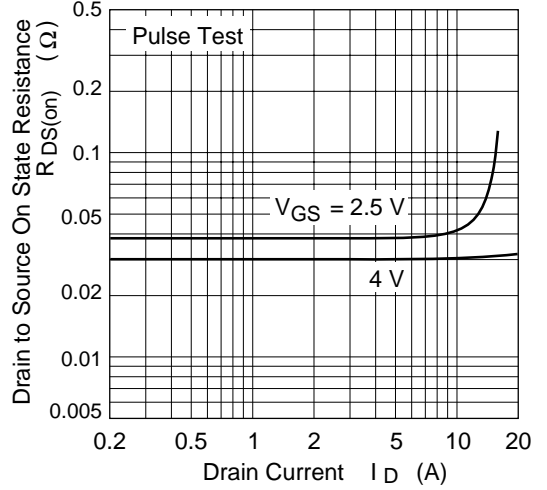
Main Characteristics



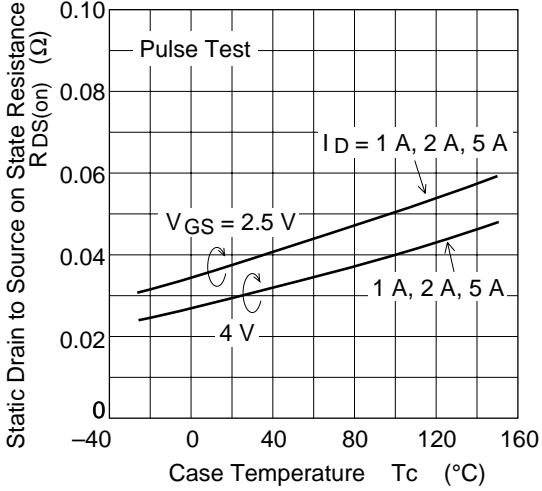
Drain to Source Saturation Voltage vs. Gate to Source Voltage



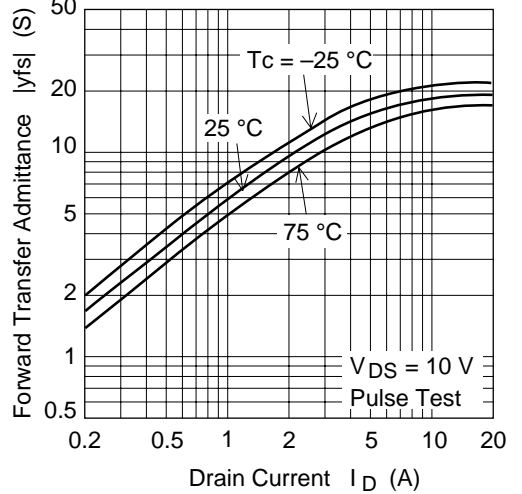
Static Drain to Source on State Resistance vs. Drain Current



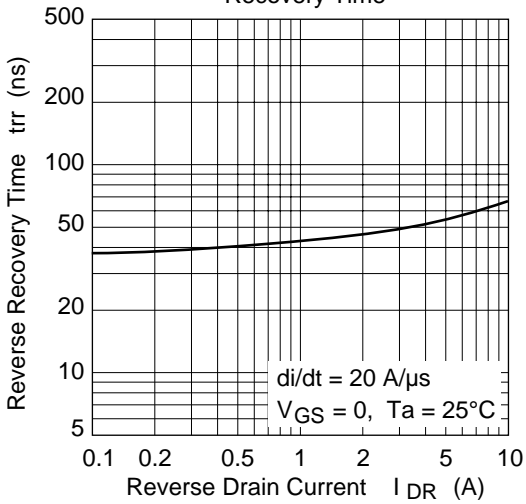
Static Drain to Source on State Resistance vs. Temperature



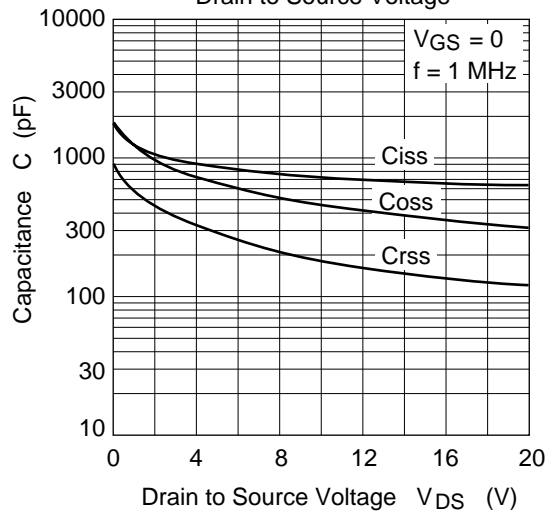
Forward Transfer Admittance vs. Drain Current



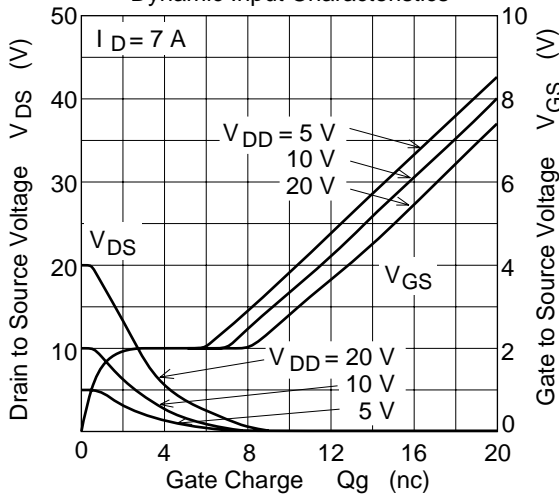
Body-Drain Diode Reverse Recovery Time



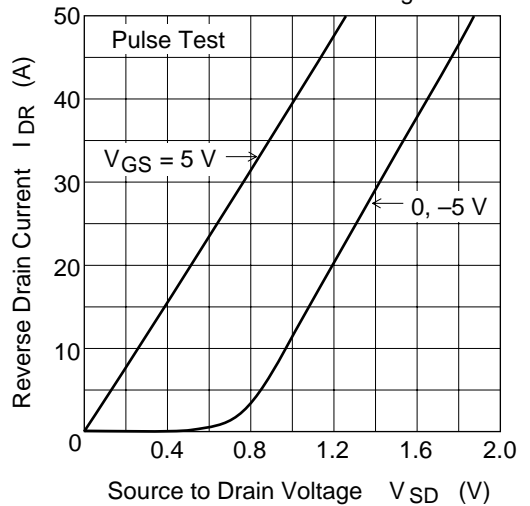
Typical Capacitance vs. Drain to Source Voltage

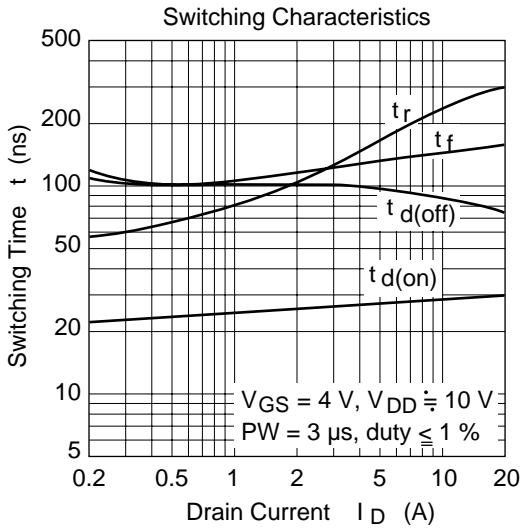


Dynamic Input Characteristics

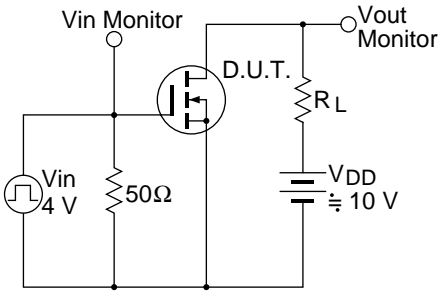


Reverse Drain Current vs. Source to Drain Voltage

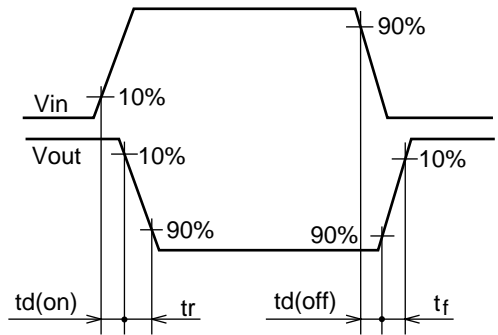


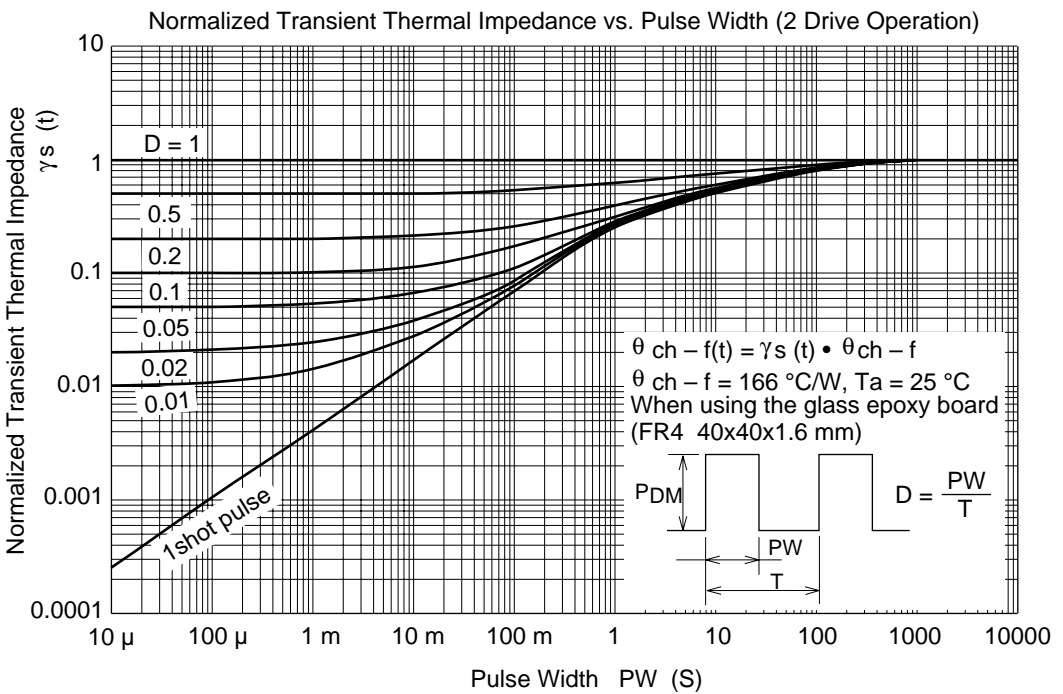
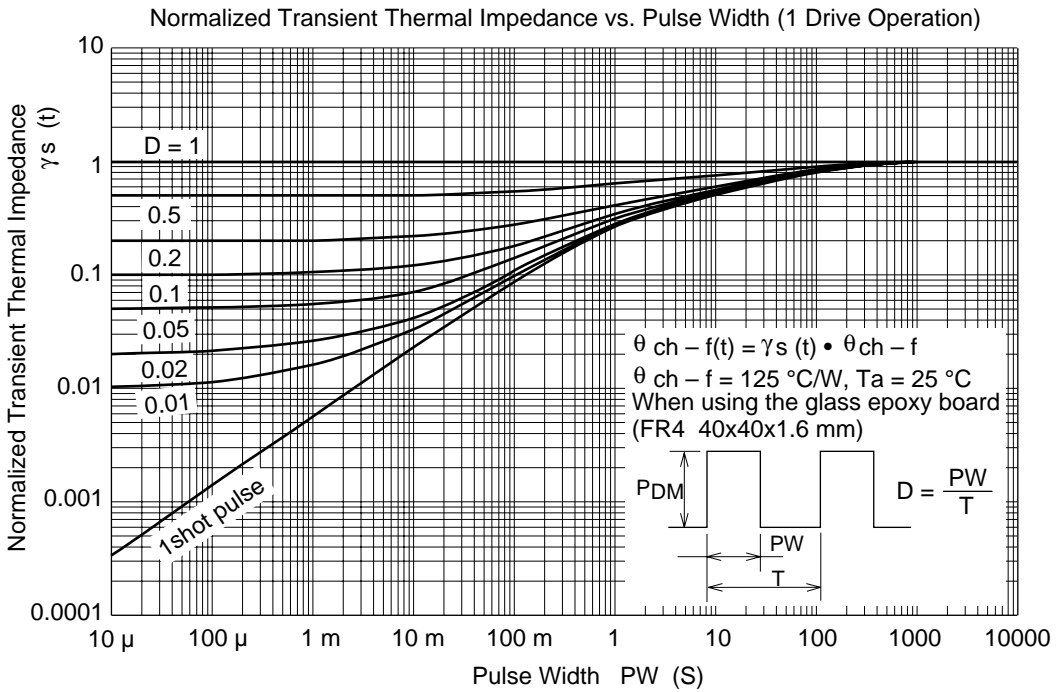


Switching Time Test Circuit



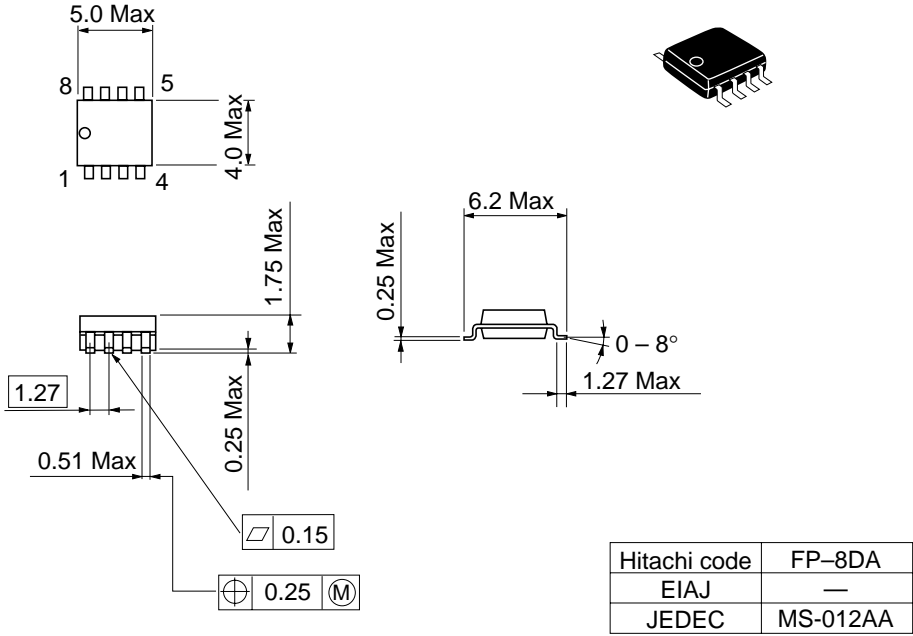
Switching Time Waveform





## Package Dimensions

Unit: mm





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## Hitachi, Ltd.

Semiconductor & Integrated Circuits.  
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan  
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL      North America      : <http://semiconductor.hitachi.com/>  
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## For further information write to:

Hitachi Semiconductor  
(America) Inc.  
179 East Tasman Drive,  
San Jose, CA 95134  
Tel: <1> (408) 433-1990  
Fax: <1> (408) 433-0223

Hitachi Europe GmbH  
Electronic components Group  
Dornacher Straße 3  
D-85622 Feldkirchen, Munich  
Germany  
Tel: <49> (89) 9 9180-0  
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.  
Electronic Components Group.  
Whitebrook Park  
Lower Cookham Road  
Maidenhead  
Berkshire SL6 8YA, United Kingdom  
Tel: <44> (1628) 585000  
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.  
16 Collyer Quay #20-00  
Hitachi Tower  
Singapore 049318  
Tel: 535-2100  
Fax: 535-1533

Hitachi Asia Ltd.  
Taipei Branch Office  
3F, Hung Kuo Building, No.167,  
Tun-Hwa North Road, Taipei (105)  
Tel: <886> (2) 2718-3666  
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.  
Group III (Electronic Components)  
7/F., North Tower, World Finance Centre,  
Harbour City, Canton Road, Tsim Sha Tsui,  
Kowloon, Hong Kong  
Tel: <852> (2) 735 9218  
Fax: <852> (2) 730 0281  
Telex: 40815 HITEC HX

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